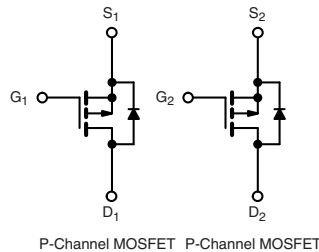
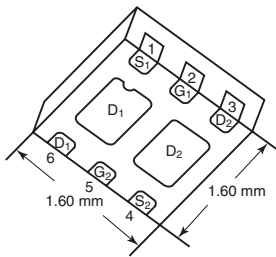




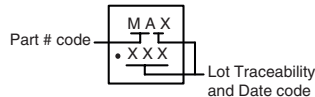
Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 20
$R_{DS(on)}$ (Ω) at $V_{GS} = - 4.5$ V	0.295
$R_{DS(on)}$ (Ω) at $V_{GS} = - 2.5$ V	0.420
$R_{DS(on)}$ (Ω) at $V_{GS} = - 1.8$ V	0.560
I_D (A) ^f	- 2.6
Configuration	Dual

PowerPAK SC75-6L-Dual



Marking Code



FEATURES

- High Quality Manufacturing Process Using SMM Process Flow
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
 - Small Footprint Area
- Compliant to RoHS Directive 2002/95/EC
- Find out more about Vishay's Medical Products at: www.vishay.com/medical-mosfets



APPLICATION EXAMPLES

- Medical Implantable Applications Including
 - Drug Delivery Systems
 - Defibrillators
 - Pacemakers
 - Hearing Aids
 - Other Implantable Devices
- Load Switch, PA Switch and Battery Switch for Portable Devices

ORDERING INFORMATION	
Package	PowerPAK SC-75
Lead (Pb)-free and Halogen-free	SMMB911DK-T1-GE3

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	- 2.6
		$T_C = 70$ °C	- 2.1
		$T_A = 25$ °C ^{a, b}	- 1.5
		$T_A = 70$ °C ^{a, b}	- 1.2
Pulsed Drain Current	I_{DM}	- 5	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C ^{a, b}	- 0.9
Maximum Power Dissipation	P_D	$T_C = 25$ °C	3.1
		$T_C = 70$ °C	2
		$T_A = 25$ °C ^{a, b}	1.1
		$T_A = 70$ °C ^{a, b}	0.7
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature) ^{c, d}		260	°C



THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Ambient ^{a, e}	$t \leq 5$ s	R_{thJA}	90	115	°C/W
Junction-to-Case (Drain)	Steady State	R_{thJC}	32	40	

Notes

- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 125 °C/W.
- Based on $T_C = 25$ °C.

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = -250$ μ A		-20	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250$ μ A		-	-19	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-	1.9	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250$ μ A		-0.4	-	-1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 8$ V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V	$V_{DS} = -20$ V	-	-	-1	μ A
		$V_{GS} = 0$ V	$V_{DS} = -20$ V, $T_J = 55$ °C	-	-	-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = -4.5$ V	$V_{DS} \leq 5$ V	5	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5$ V	$I_D = -1.5$ A	-	0.242	0.295	Ω
		$V_{GS} = -2.5$ V	$I_D = -1.2$ A	-	0.345	0.420	
		$V_{GS} = -1.8$ V	$I_D = -0.18$ A	-	0.455	0.560	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10$ V, $I_D = -1.5$ A		-	3	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0$ V	$V_{DS} = -10$ V, $f = 1$ MHz	-	115	-	pF
Output Capacitance	C_{oss}			-	30	-	
Reverse Transfer Capacitance	C_{rss}			-	20	-	
Total Gate Charge	Q_g	$V_{GS} = -8$ V	$V_{DS} = -10$ V, $I_D = -1.7$ A	-	2.6	4.0	nC
Gate-Source Charge	Q_{gs}	$V_{GS} = -4.5$ V	$V_{DS} = -10$ V, $I_D = -1.7$ A	-	1.6	2.5	
Gate-Drain Charge	Q_{gd}			-	0.3	-	
Gate Resistance	R_g	$f = 1$ MHz		-	7	-	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10$ V, $R_L = 7.1$ Ω $I_D \cong -1.4$ A, $V_{GEN} = -4.5$ V, $R_g = 1$ Ω		-	12	20	ns
Rise Time	t_r			-	45	70	
Turn-Off Delay Time	$t_{d(off)}$			-	10	15	
Fall Time	t_f			-	31	50	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10$ V, $R_L = 7.1$ Ω $I_D \cong -1.4$ A, $V_{GEN} = -8$ V, $R_g = 1$ Ω		-	3	10	
Rise Time	t_r			-	25	40	
Turn-Off Delay Time	$t_{d(off)}$			-	10	15	
Fall Time	t_f			-	10	15	
Source-Drain Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C		-	-	-2.6	A
Pulse Diode Forward Current	I_{SM}			-	-	5	



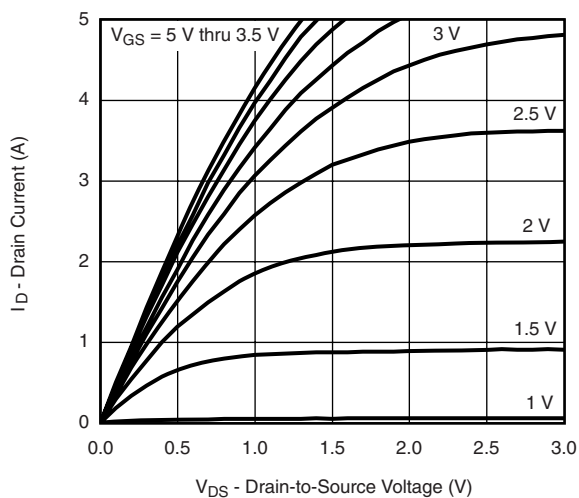
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Source-Drain Body Diode Characteristics						
Body Diode Voltage	V_{SD}	$I_S = -1.4\text{ A}$, $V_{GS} = 0\text{ V}$	-	-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1.4\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	-	25	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	26	50	nC
Reverse Recovery Fall Time	t_a		-	19	-	ns
Reverse Recovery Rise Time	t_b		-	6	-	

Notes

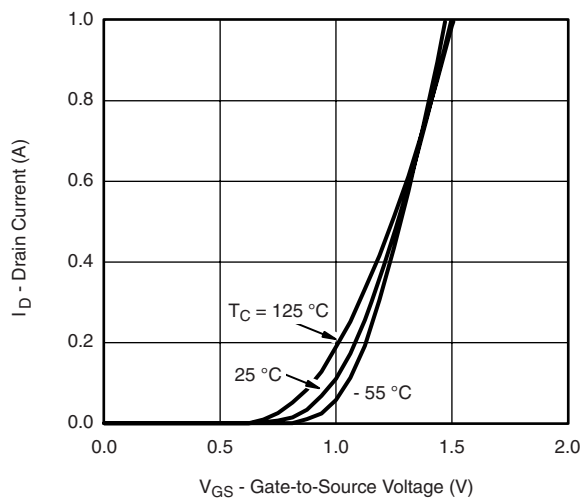
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

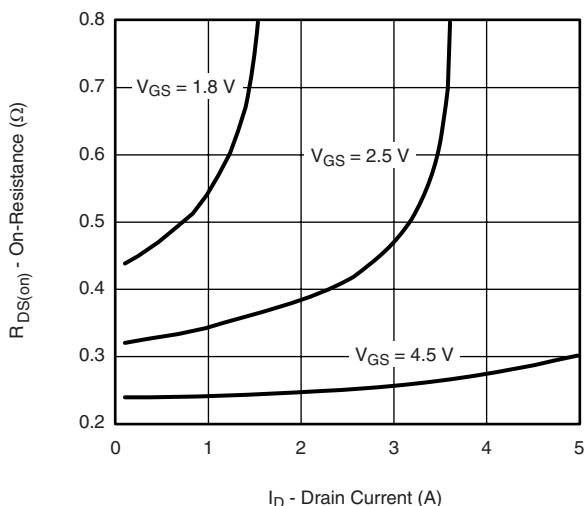
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



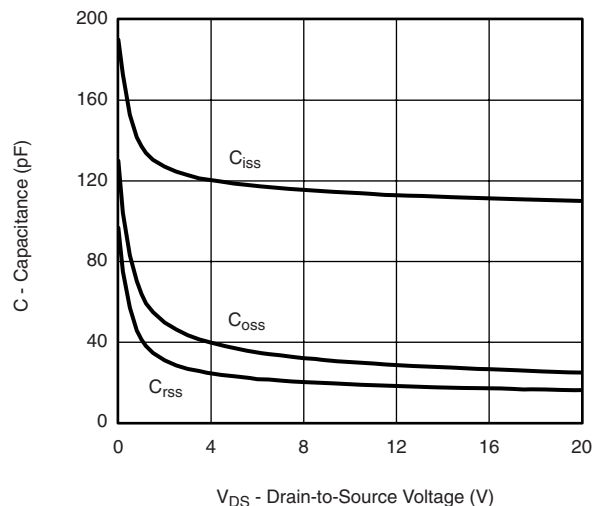
Output Characteristics



Transfer Characteristics



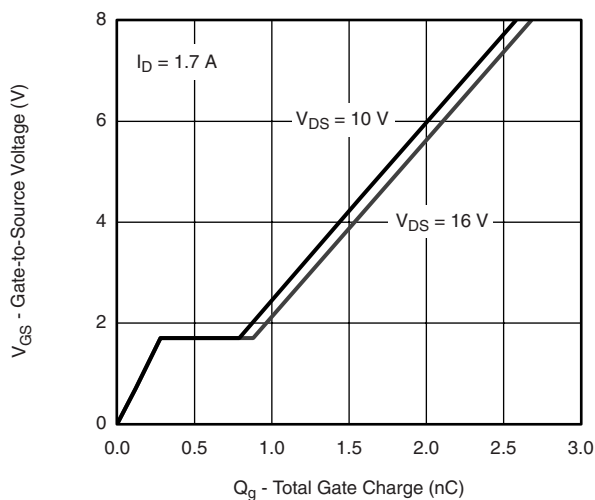
On-Resistance vs. Drain Current and Gate Voltage



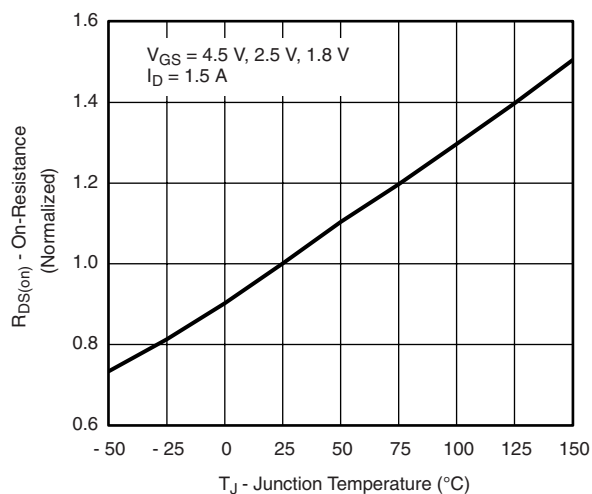
Capacitance



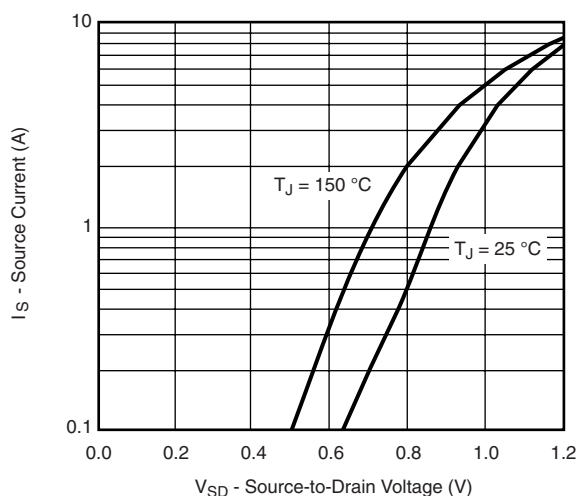
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



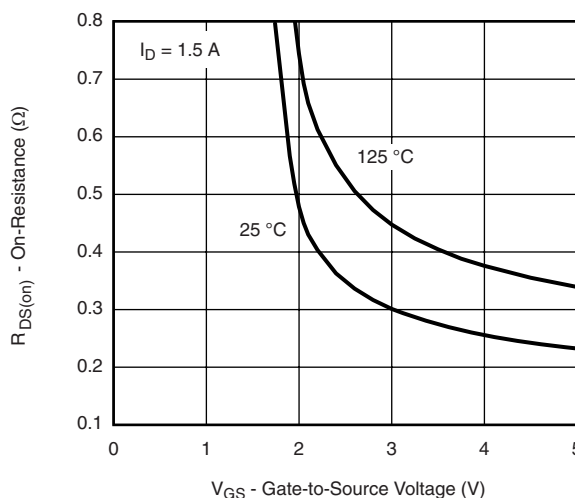
Gate Charge



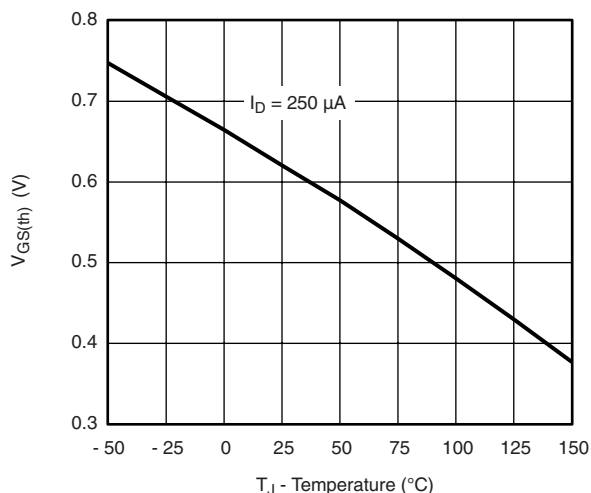
On-Resistance vs. Junction Temperature



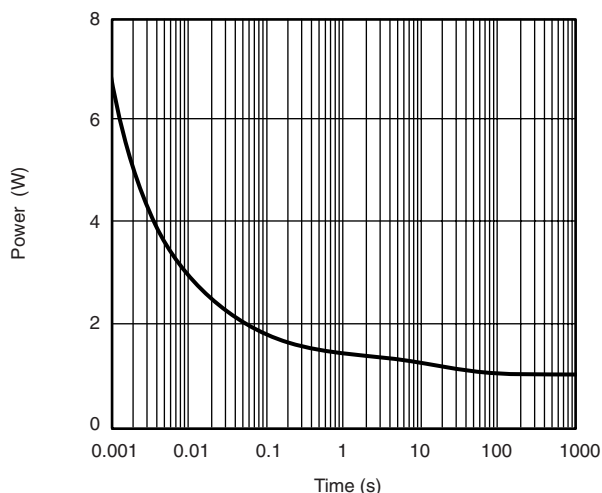
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



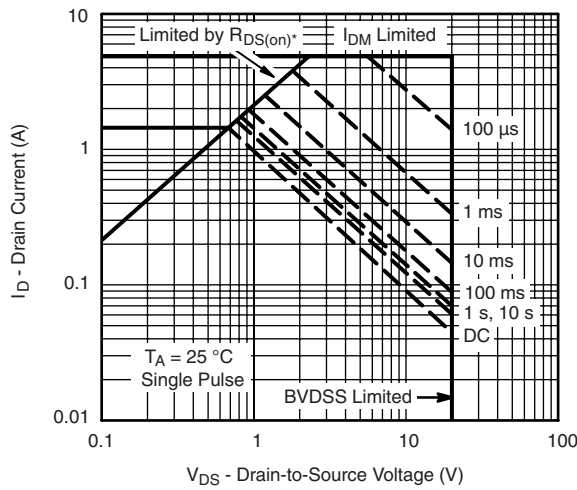
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

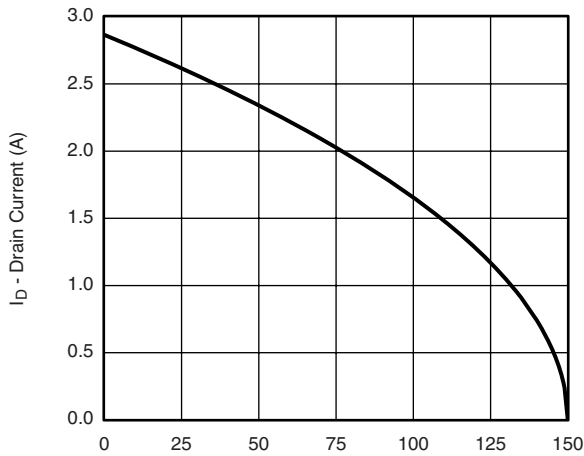


TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



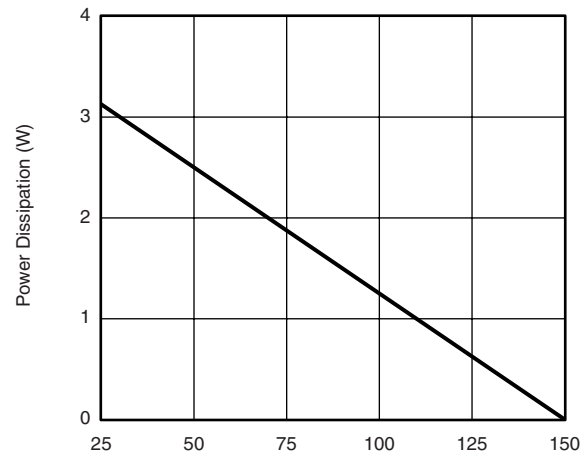
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature ($^\circ\text{C}$)

Current Derating*

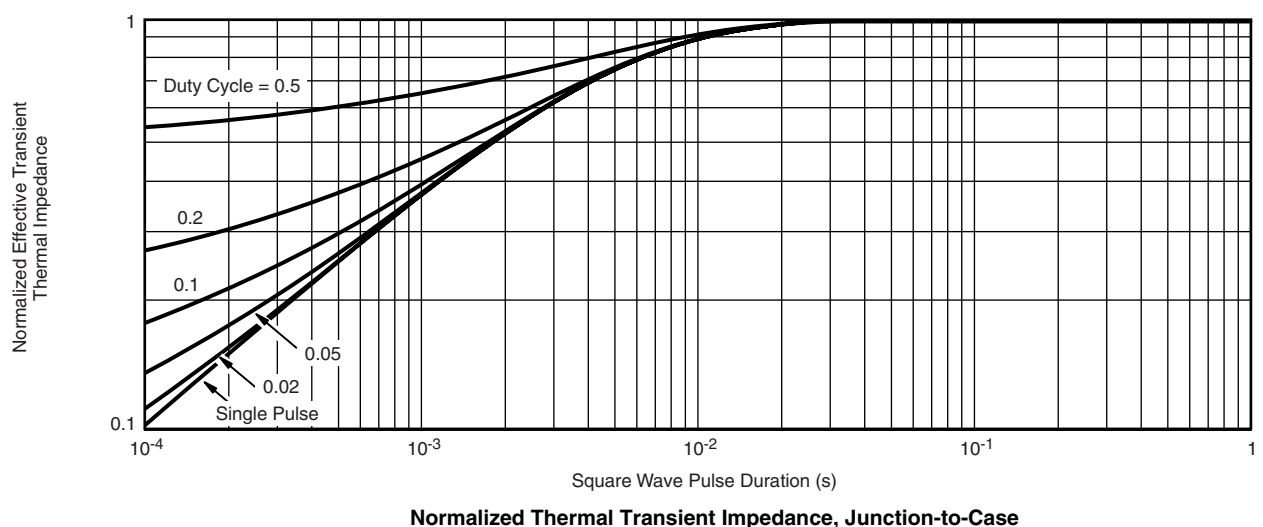
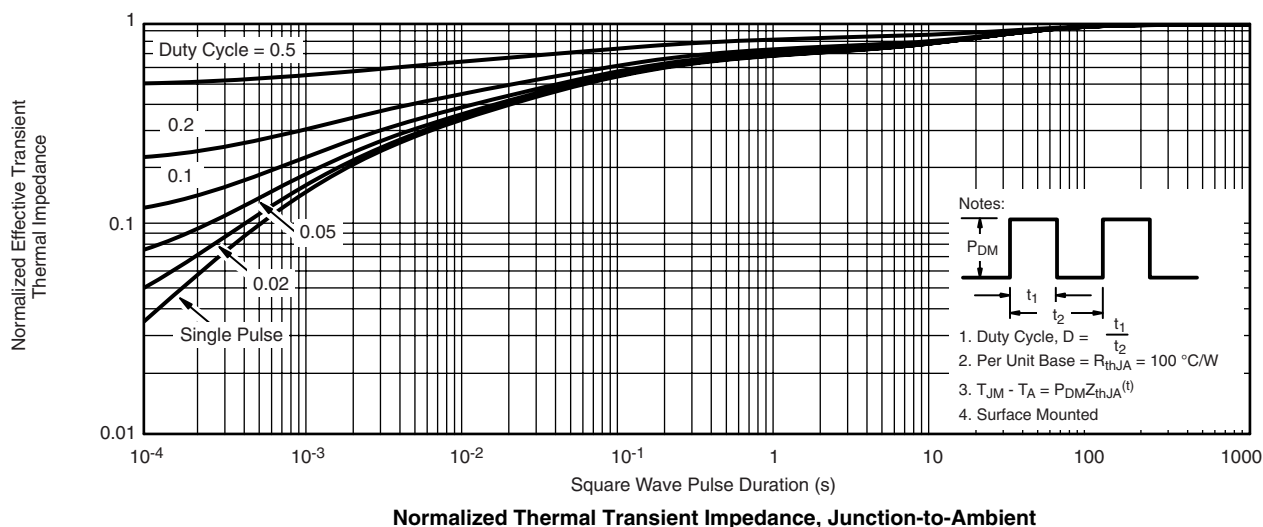


T_C - Case Temperature ($^\circ\text{C}$)

Power Derating

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65174.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.